

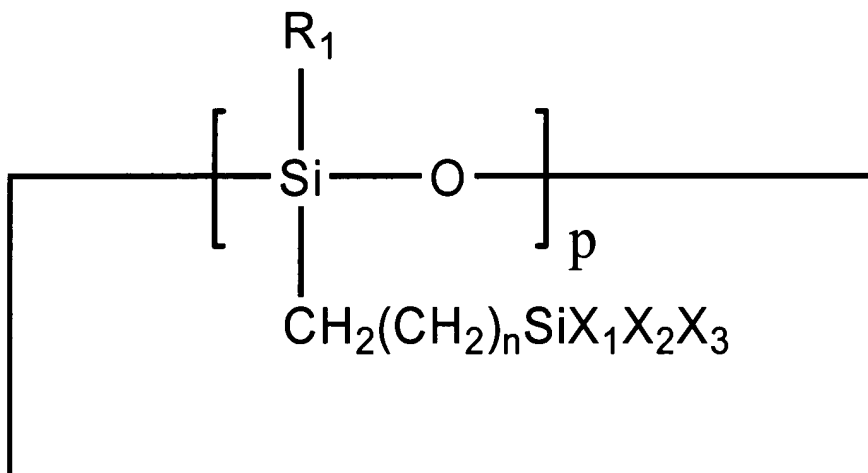
AMENDMENTS TO THE CLAIMS

The following is a complete, marked up listing of revised claims with a status identifier in parentheses, underlined text indicating insertions, and strikethrough and/or double-bracketed text indicating deletions.

LISTING OF CLAIMS

1. (Currently Amended) A siloxane-based resin prepared by hydrolyzing and polycondensing a first monomer of the Formula 1 and a second monomer of the Formula 2 in an organic solvent in the presence of an acid or alkaline catalyst and water:

Formula 1



wherein,

- R_1 is a hydrogen atom, a C_{1-3} alkyl group or a C_{6-15} aryl group;
each of X_1 , X_2 and X_3 , independently, is a C_{1-3} alkyl group, a C_{1-10} alkoxy group or a halogen atom, provided that at least one of them is hydrolysable;
 m is an integer from 0 to 10; and
 p is an integer from 3 to 8, and

Formula 2



wherein,

- R_2 is a hydrogen atom, a C_{1-3} alkyl group, or a C_{6-15} aryl group;
 X_4 is a C_{1-10} alkoxy group or a halogen atom; and
 a is an integer of 1-4~~1-3~~,

2. (Original) The siloxane-based resin according to claim 1, wherein the molar ratio of the first monomer of Formula 1 to the second monomer of Formula 2 is 1:99-99:1.

3. (Original) The siloxane-based resin according to claim 1, wherein the Mw of the resin is 3,000-300,000.

Claims 4-8. (Cancelled)

9. (Original) An interlayer insulating film for a semiconductor device comprising the siloxane-based resin of claim 1.

10. (Original) The interlayer insulating film according to claim 9, wherein micropores are formed throughout the film by the use of a porogen.

11. (Original) A semiconductor device containing an interlayer insulating film comprising the siloxane-based resin of claim 1.

12. (Original) The siloxane-based resin of claim 1, having a dielectric constant of 3 or less.

Claim 13. (Cancelled)

14. (Original) The interlayer insulating film of claim 9, having a dielectric constant of 3.0 or less.

15. (Previously Presented) The siloxane-based resin according to claim 1, wherein the organic solvent is selected from the group consisting of hexane, anisole, mesitylene, xylene, methyl isobutyl ketone, 1-methyl-2-pyrrolidinone, acetone, cyclohexanone, tetrahydrofuran, isopropyl ether, ethyl acetate, butyl acetate, propylene glycol methyl ether acetate, isopropyl alcohol, butyl alcohol, dimethylacetamide, dimethylformamide, silicon-based solvents and mixtures thereof.

16. (Previously Presented) The siloxane-based resin according to claim 1, wherein the catalyst

is selected from the group consisting of hydrochloric acid, nitric acid, benzene sulfonic acid, oxalic acid, formic acid, potassium hydroxide, sodium hydroxide, triethylamine, sodium bicarbonate and pyridine.

17. (Previously Presented) The siloxane-based resin according to claim 1, wherein the siloxane based resin is combined with a porogen selected from the group consisting of cyclodextrine, polycaprolactone and mixtures thereof.